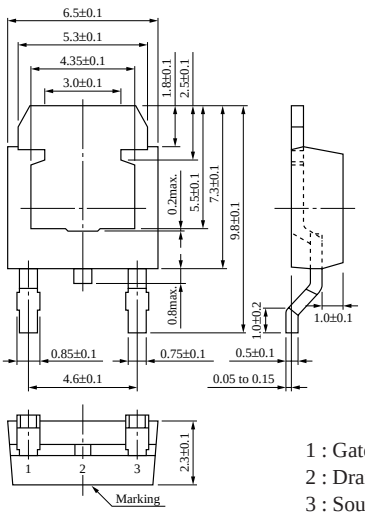
2SK2474

Silicon N-Channel MOS

For high-speed switching

Unit : mm



1 : Gate
2 : Drain
3 : Source
EIAJ : SC-63
U Type Package

■ Features

- Low ON-resistance $R_{DS(on)}$
- High-speed switching
- High drain-source voltage (V_{DSS})

■ Absolute Maximum Ratings (Tc = 25˚C)

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	V_{DSS}	250	V
Gate-Source voltage	V_{GSS}	±30	V
Drain current	I_D	±2	A
Max drain current	I_{DP}	±4	A
Allowable power dissipation	P_D *	10	W
Channel temperature	T_{ch}	150	˚C
Storage temperature	T_{stg}	–55 to +150	˚C

* T_C= 25˚C

■ Electrical Characteristics (Tc = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	V_{DS}= 200V, V_{GS}= 0			0.1	mA
Gate-Source leakage current	I_{GSS}	V_{GS}= ±30V, V_{DS}= 0			±1	µA
Drain-Source breakdown voltage	V_{DSS}	I_D=1mA, V_{GS}= 0	250			V
Gate threshold voltage	V_{th}	V_{DS}=10V, I_D=1mA	1		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=1A		1.2	2	Ω
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}= 25V, I_D=1A	0.5	1		S
Input capacitance	C_{iss}	V_{DS}=10V, V_{GS}= 0, f=1MHz		280		pF
Output capacitance	C_{oss}			80		pF
Feedback capacitance	C_{rss}			30		pF
Turn-on time	t_{on}	V_{GS}=10V, I_D=1A, V_{DD}=100V, R_L=100Ω		30		ns
Fall time	t_f			45		ns
Turn-off time (delay time)	$t_{d(off)}$			90		ns